

Ver.1.2

Diagonal 9.2 mm (Type 1 / 1.7) CMOS solid-state Image Sensor with Square Pixel for Monochrome Cameras

Description

The IMX430LLJ is a diagonal 9.2 mm (Type 1 / 1.7) CMOS active pixel type solid-state image sensor with a square pixel array and 2.03 M effective pixels. This chip features a global shutter with variable charge-integration time. This chip operates with analog 3.3 V, digital 1.2 V, and interface 1.8 V triple power supply, and has low power consumption. High sensitivity, low dark current and low PLS characteristics are achieved.
(Applications: FA cameras, ITS cameras)

Features

- ◆ CMOS active pixel type dots
- ◆ Built-in timing adjustment circuit, H/V driver and serial communication circuit
- ◆ Global shutter function
- ◆ Input frequency
37.125 MHz / 74.25 MHz / 54 MHz
- ◆ Number of recommended recording pixels: 1624 (H) × 1240 (V) approx. 2.01 M pixels
 - Readout mode
 - All-pixel scan mode
 - Vertical / Horizontal 1 / 2 Subsampling mode
 - 2 × 2 Vertical FD binning mode
 - ROI mode
 - Vertical / Horizontal - Normal / Inverted readout mode
- ◆ Readout rate
 - Maximum frame rate in
 - All-pixel scan mode: 12 bit: 132.0 frame/s
- ◆ 12-bit A/D converter
- ◆ CDS / PGA function
 - 0 dB to 24 dB: Analog Gain (0.1 dB step)
 - 24.1 dB to 48 dB: Analog Gain: 24 dB + Digital Gain: 0.1 dB to 24 dB (0.1 dB step)
- ◆ I/O interface
 - SLVS (2 ch / 4 ch switching) output (594 / 297 Mbps per ch)
 - SLVS - EC (1 Lane / 2 Lane switching) output (2.376 / 1.188 Gbps per Lane)
- ◆ Recommended lens F number: 2.8 or more (Close side)
- ◆ Recommended exit pupil distance: -100 mm to $-\infty$

Pregius

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Device Structure

- ◆ CMOS image sensor
- ◆ Image size Diagonal 9.2 mm (Type 1 / 1.7) Approx. 2.03 M pixels All-pixel
- ◆ Total number of pixels 1632 (H) × 1264 (V) Approx. 2.06 M pixels
- ◆ Number of effective pixels 1632 (H) × 1248 (V) Approx. 2.03 M pixels
- ◆ Number of active pixels 1632 (H) × 1248 (V) Approx. 2.03 M pixels
- ◆ Number of recommended recording pixels 1624 (H) × 1240 (V) Approx. 2.01 M pixels All-pixel
- ◆ Unit cell size 4.5 μm (H) × 4.5 μm (V)
- ◆ Optical black Horizontal (H) direction: Front 0 pixel, rear 0 pixel
Vertical (V) direction: Front 16 pixels, rear 0 pixel
- ◆ Package 226 pin LGA

Image Sensor Characteristics

(Tj = 60 °C)

Item		Value	Remarks
Sensitivity (F8)	Typ.	1677 mV	1/30 s accumulation
Saturation signal	Min.	1001 mV	

Basic Drive Mode

Drive mode	Recommended number of recording pixels	Maximum frame rate [frame/s]	Output interface	ADC [bit]
All pixel	1624 (H) × 1240 (V) approx. 2.01 M pixels	89.1	SLVS 4 ch	12
		132.0	SLVS – EC 2 Lane	
Vertical / Horizontal 1/2 subsampling	812 (H) × 620 (V) approx. 0.50 M pixels	268.0	SLVS 4 ch	12
		268.0	SLVS – EC 2 Lane	
2 × 2 Vertical FD binning	812 (H) × 620 (V) approx. 0.50 M pixels	268.0	SLVS 4 ch	12
		268.0	SLVS – EC 2 Lane	

